

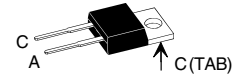
Gallium Arsenide Schottky Rectifier

$I_{FAV} = 18 \text{ A}$
 $V_{RRM} = 220/250 \text{ V}$
 $C_{Junction} = 26 \text{ pF}$

Preliminary Data

V_{RSM} V	V_{RRM} V	Type
220	220	DGS 20-022A
250	250	DGS 20-025A

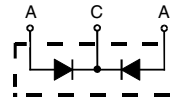
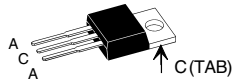
} Single


TO-220 AC


A = Anode, C = Cathode, TAB = Cathode

V_{RSM} V	V_{RRM} V	Type
220	220	DGSK 40-022A
250	250	DGSK 40-025A

} Common cathode


TO-220 AB


Symbol	Conditions	Maximum Ratings	
I_{FAV}	$T_C = 25^\circ\text{C}$; DC	18	A
I_{FAV}	$T_C = 90^\circ\text{C}$; DC	13	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$; $t_p = 10 \text{ ms}$ (50 Hz), sine	30	A
T_{VJ}		-55...+175	$^\circ\text{C}$
T_{stg}		-55...+150	$^\circ\text{C}$
P_{tot}	$T_C = 25^\circ\text{C}$	48	W
M_d	mounting torque	0.4...0.6	Nm

Features

- Low forward voltage
- Very high switching speed
- Low junction capacity of GaAs
 - low reverse current peak at turn off
- Soft turn off
- Temperature independent switching behaviour
- High temperature operation capability
- Epoxy meets UL 94V-0

Applications

- MHz Switched mode power supplies (SMPs)
- Small size SMPs
- High frequency converters
- Resonant converters

Symbol	Conditions	Characteristic Values	
		typ.	max.
I_R ①	$T_{VJ} = 25^\circ\text{C}$ $V_R = V_{RRM}$ $T_{VJ} = 125^\circ\text{C}$ $V_R = V_{RRM}$	2.0	2.0 mA mA
V_F	$I_F = 7.5 \text{ A}$; $T_{VJ} = 125^\circ\text{C}$	1.3	V
	$I_F = 7.5 \text{ A}$; $T_{VJ} = 25^\circ\text{C}$	1.2	1.5 V
C_J	$V_R = 100 \text{ V}$; $T_{VJ} = 125^\circ\text{C}$	26	pF
R_{thJC}		3.1	K/W
R_{thCH}		0.5	K/W
Weight		2	g

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %
 Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, Conditions and dimensions.

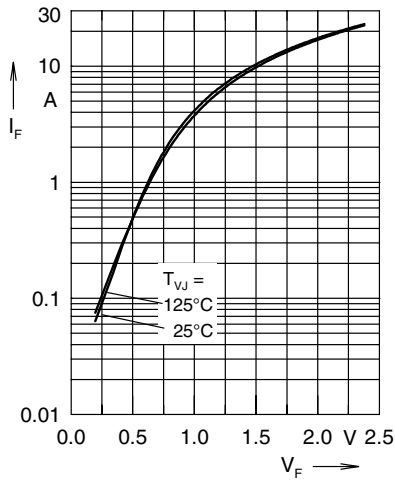


Fig. 1 typ. forward characteristics

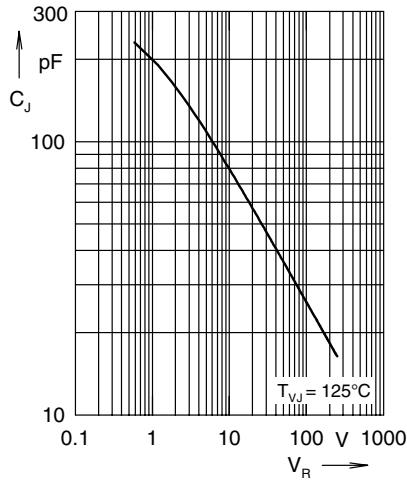


Fig. 2 typ. junction capacity versus blocking voltage

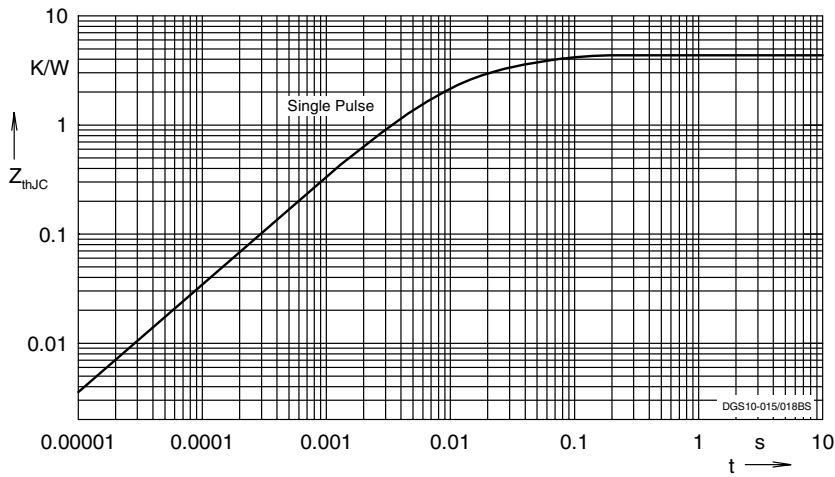
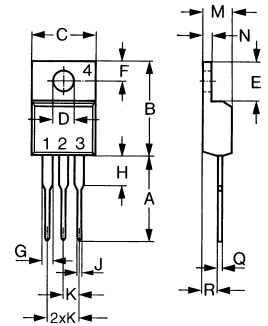


Fig. 3 typ. thermal impedance junction to case

Note:
explanatory comparison of the basic operational behaviour of rectifier diodes and Gallium Arsenide Schottky diodes:

	Rectifier Diode	GaAs Schottky Diode
conduction	by majority + minority carriers	by majority carriers only
forward characteristics	$V_F (I_F)$	$V_F (I_F)$, see Fig. 1
turn off characteristics	extraction of excess carriers causes temperature dependant reverse recovery (t_{rr} , I_{RM} , Q_{rr})	reverse current charges junction capacity C_J , see Fig. 2;
turn on characteristics	delayed saturation leads to V_{FR}	not temperature dependant no turn on overvoltage peak

Outline (center pin only for DGSK types)



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.38	0.56	0.015	0.022
R	2.29	2.79	0.090	0.110